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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: 2824
Examiner: To Be Assigned

In Re PATENT APPLICATION of:

Applicant(s): Kun-Hong CHEN

Serial No.: 10/781,778

Filed: February 20, 2004

For: METHOD FOR FABRICATING A LOW
TEMPERATURE POLYSILICON THIN
FILM TRANSISTOR

Atty Ref.: SUND 502

**INFORMATION
DISCLOSURE
STATEMENT**

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

This is an information disclosure statement submitted in compliance with the timing requirements of 37 C.F.R. §1.97(b)(3), i.e., prior to a first Office Action on the merits.

Attached is a copy of an English-language article, which was cited by the Taiwanese Patent Office in an Office Action, mailed on June 17, 2004, which was issued in connection with a Taiwanese counterpart application. Any relevance of the article is self-evident. Also, listed for consideration is U.S. patent number US 6,562,670 B2, which was also cited in the above-mentioned Taiwanese Office Action. The article and U.S. patent are listed on the attached Form PTO-1449.

Since this Information Disclosure Statement is being filed before a first Office Action, no certification or fee is required, and the requirements of 37 C.F.R. §§1.97 and 1.98 are deemed to be fully met as to all documents listed. Consideration of the listed documents respectfully is requested.

Should any fee be required, please charge the same to our Deposit Account No. 18-0002 and notify us accordingly.

Respectfully submitted,

November 2, 2004
Date

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FBI ENCLOSED:\$
Please charge any further
fee to our Deposit Account
No. 18-0002



FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT		Atty. Docket		Application No.			
		SUND 502		10/781,778			
		Applicant Kun-Hong CHEN		Filing Date February 20, 2004			
		Group 2824					
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date
	AA	6,562,670	05/13/03	SHIH			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub-Class	Translation
	AI						
	AJ						
	AK						
	AL						
OTHER (Including Author, Title, Date, Pertinent Pages, etc.)							
	AM	"High-speed Semiconductor Devices" ("Heterostructure Field-Effect Transistors"): International Electron Devices and Materials Symposium; National Sun Yat-sen University, Kaohsiung, Taiwan, R.O.C.; 1988; 3 pages					
	AN						
Examiner					Date Considered		
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							